

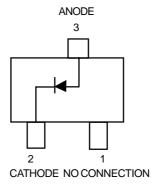
Single Silicon Switching Diodes

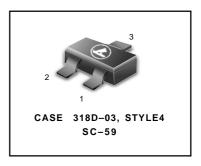
These Silicon Epitaxial Planar Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC-59 package which is designed for low power surface mount applications.

- Fast t_{rr}, < 3.0 ns
- Low C_D , < 2.0 pF
- Available in 8 mm Tape and Reel
 Use M1MA151/2AT1 to order the 7 inch/3000 unit reel.
 Use M1MA151/2AT3 to order the 13 inch/10,000 unit reel.

M1MA151AT1 M1MA152AT1

SC-59 PACKAGE SINGLE SILICON SWITCHING DIODES 40/80 V-100mA SURFACE MOUNT





MAXIMUM R ATINGS $(T_A = 25^{\circ}C)$

Rating		Symbol	Value	Unit
Reverse Voltage	M1MA151AT1	V _R	40	Vdc
	M1MA152AT1		80	
Peak Reverse Voltage	M1MA151AT1	V _{RM}	40	Vdc
	M1MA152AT1		80	
Forward Current		I _F	100	mAdc
Peak Forward Current		I _{FM}	225	mAdc
Peak Forward Surge Current		_{FSM} ⁽¹⁾	500	mAdc

THERMAL CHARACTERISTICS

Rating	Symbo	lMax	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	TJ	150	℃
Storage Temperature	T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic		Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	M1MA151AT1	I _R	V _R = 35 V		0.1	μAdc
	M1MA152AT1		$V_R = 75 V$	_	0.1	
Forward Voltage		V _F	$I_F = 100 \text{ mA}$	_	1.2	Vdc
Reverse Breakdown Voltage	M1MA151AT1	V _R	I _R = 100 μA	40	_	Vdc
	M1MA152AT1			80	_	
Diode Capacitance		Съ	$V_R = 0, f = 1.0 \text{ MHz}$	_	2.0	pF
Reverse Recovery Time		t _{rr} (2)	$I_F = 10 \text{ mA}, V_R = 6.0 \text{ V},$	_	3.0	ns
			$R_L = 100\Omega, I_{rr} = 0.1 I_R$			

1. t = 1 SEC

2. t , Test Circuit

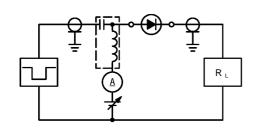


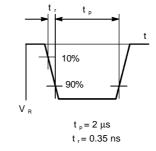
M1MA151AT1 M1MA152AT1

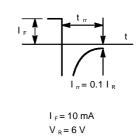
RECOVERY TIME EQUIVALENT TEST CIRCUIT

INPUT PULSE

OUTPUT PULSE

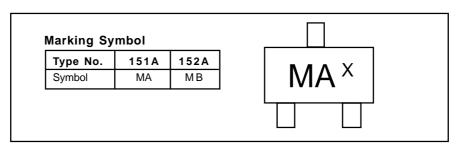






R $_{L}$ = 100 Ω

DEVICE MARKING



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.